

October 1996

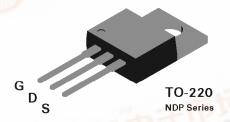
NDP5060 / NDB5060 N-Channel Enhancement Mode Field Effect Transistor

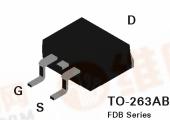
General Description

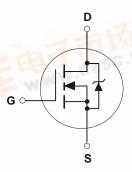
These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulses in the avalanche and commutation modes. These devices are particularly suited for low voltage applications such as automotive, DC/DC converters, PWM motor controls, and other battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

Features

- 26 A, 60 V. $R_{DS(ON)} = 0.05 \Omega$ @ $V_{GS} = 10 V$.
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- 175°C maximum junction temperature rating.
- High density cell design for extremely low R_{DS(ON)}.
- TO-220 and TO-263 (D²PAK) package for both through hole and surface mount applications.







Absolute Maximum Ratings

 $T_{\rm C} = 25^{\circ}{\rm C}$ unless otherwise note

Symbol	Parameter	NDP5060	NDB5060	Units			
V _{DSS}	Drain-Source Voltage	60					
V_{DGR}	Drain-Gate Voltage ($R_{GS} \le 1 \text{ M}\Omega$)	60 60 07.5					
V _{GSS}	Gate-Source Voltage - Continuous	±20					
	- Nonrepetitive (t _P < 50 μs)	±4	.0				
I _D	Drain Current - Continuous	20	6	Α			
	- Pulsed	78	8				
P _D	Total Power Dissipation @ T _c = 25°C	6	8	W			
100	Derate above 25°C	0.4	15	W/°C			
T_J, T_{STG}	Operating and Storage Temperature Range	-65 to	175	°C			

Symbol	Parameter	Conditions	Min	Тур	Max	Units	
DRAIN-S	OURCE AVALANCHE RATINGS (Note 1)			•	•	•	•
W _{DSS}	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 30 \text{ V}, I_{D} = 26 \text{ A}$				100	mJ
I _{AR}	Maximum Drain-Source Avalanche Curre	ent				26	Α
OFF CH	ARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$		60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 60 V, V _{GS} = 0 V				250	μΑ
			T _J = 125°C			1	mA
I _{GSSF}	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$				100	nA
I _{GSSR}	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$				-100	nA
ON CHAI	RACTERISTICS (Note 1)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		2	2.9	4	V
			T _J = 125°C	1.4	2.2	2.8	
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_{D} = 13 \text{ A}$			0.04	0.05	Ω
				0.07	0.08		
I _{D(on)}	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 10 \text{ V}$	$V_{GS} = 10 \text{ V}, V_{DS} = 10 \text{ V}$				Α
g _{FS}	Forward Transconductance	$V_{DS} = 10 \text{ V}, I_{D} = 13 \text{ A}$			9		S
DYNAMI	CCHARACTERISTICS						
C _{iss}	Input Capacitance	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V},$	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		630		pF
C _{oss}	Output Capacitance	† = 1.0 MHz			225		pF
C _{rss}	Reverse Transfer Capacitance				70		pF
SWITCHI	NG CHARACTERISTICS (Note 1)	<u> </u>		•	•	•	•
t _{D(on)}	Turn - On Delay Time	$V_{DD} = 30 \text{ V}, I_{D} = 26 \text{ A},$		9	20	nS	
t,	Turn - On Rise Time	V_{GS} = 10 V, R_{GEN} = 15 Ω		95	200	nS	
t _{D(off)}	Turn - Off Delay Time			19	40	nS	
t _f	Turn - Off Fall Time				48	100	nS
$\overline{Q_g}$	Total Gate Charge	$V_{DS} = 24 \text{ V},$ $I_{D} = 26 \text{ A}, V_{GS} = 10 \text{ V}$			20	40	nC
$\overline{Q_{gs}}$	Gate-Source Charge	$I_D = 26 \text{ A}, \ V_{GS} = 10 \text{ V}$		5		nC	
Q_{gd}	Gate-Drain Charge			11		nC	

Symbol	Parameter	Conditions	Min	Тур	Max	Units
DRAIN-S	OURCE DIODE CHARACTERISTICS		·			
I _s	Maximum Continuos Drain-Source Diode			26	Α	
I _{SM}	Maximum Pulsed Drain-Source Diode Fo			78	Α	
V_{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 13 A (Note 1)		0.9	1.3	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_F = 26 \text{ A},$		54	120	ns
I _{rr}	Reverse Recovery Current	$dl_{F}/dt = 100 \text{ A/}\mu\text{s}$		2.1	8	А
THERMA	AL CHARACTERISTICS	•		•		•
R _{eJC}	Thermal Resistance, Junction-to-Case			2.2	°C/W	
R _{BJA}	Thermal Resistance, Junction-to-Ambier			62.5	°C/W	

Note: 1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

Typical Electrical Characteristics

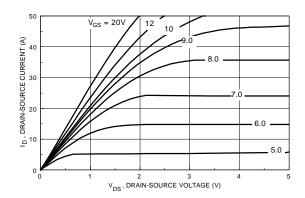
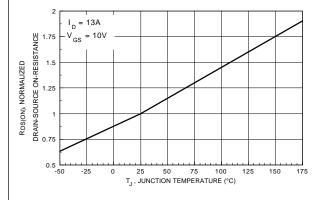


Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.



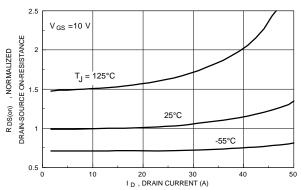
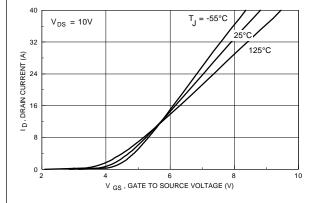


Figure 3. On-Resistance Variation with Temperature.

Figure 4. On-Resistance Variation with Drain Current and Temperature.



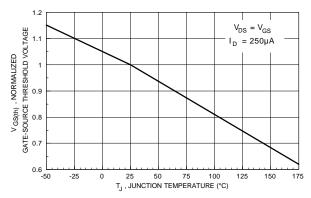


Figure 5. Transfer Characteristics.

Figure 6. Gate Threshold Variation with Temperature.

Typical Electrical Characteristics (continued)

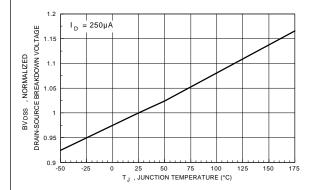


Figure 7. Breakdown Voltage Variation with Temperature.

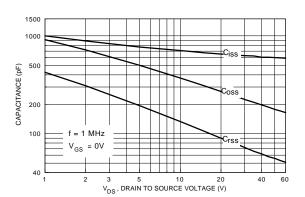


Figure 9. Capacitance Characteristics.

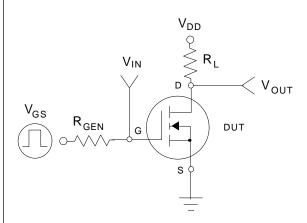


Figure 11. Switching Test Circuit.

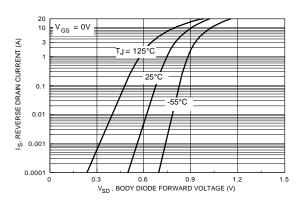


Figure 8. Body Diode Forward Voltage
Variation with Current and Temperature.

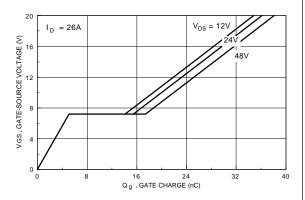


Figure 10. Gate Charge Characteristics.

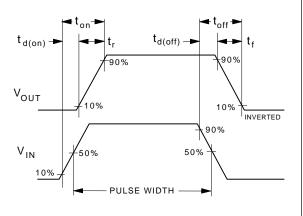
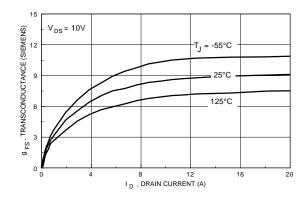


Figure 12. Switching Waveforms.

Typical Electrical Characteristics (continued)



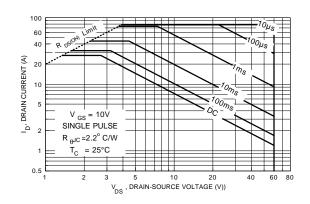


Figure 13. Transconductance Variation with Drain Current and Temperature.

Figure 14. Maximum Safe Operating Area.

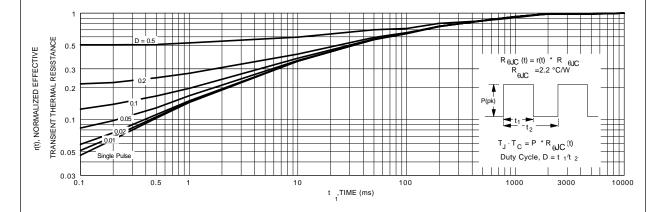
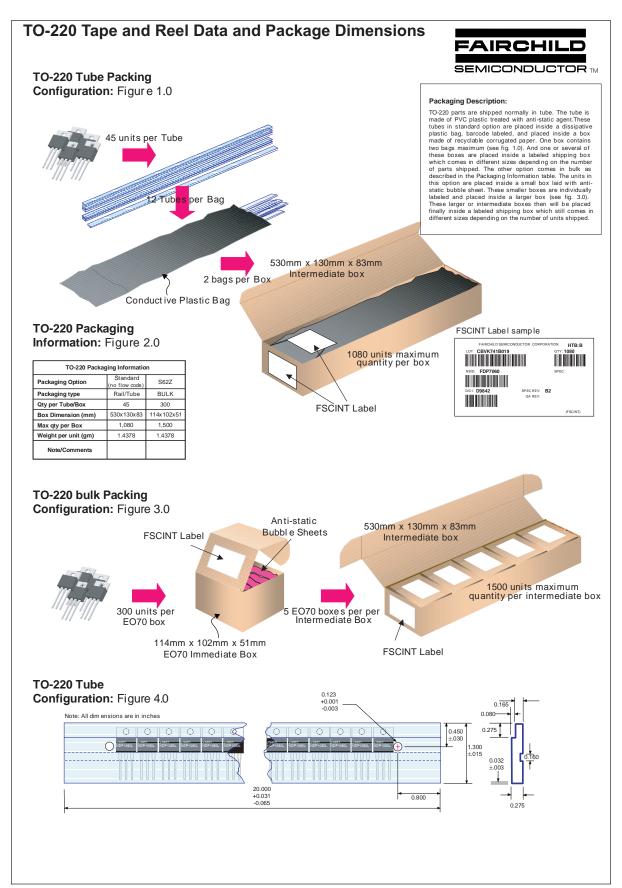
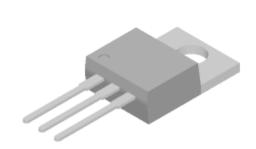


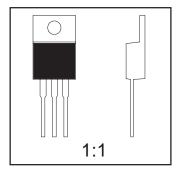
Figure 15. Transient Thermal Response Curve.



TO-220 Tape and Reel Data and Package Dimensions, continued

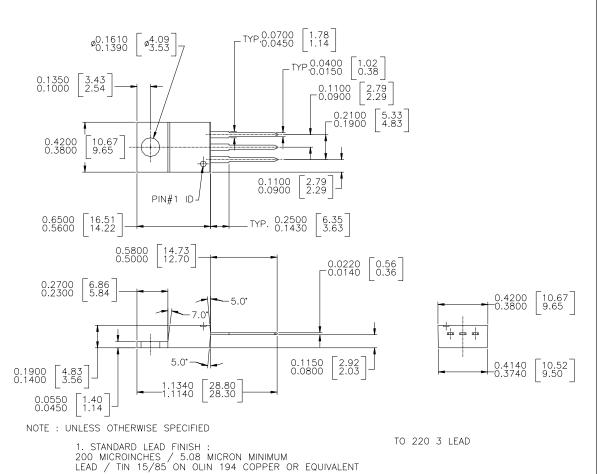
TO-220 (FS PKG Code 37)



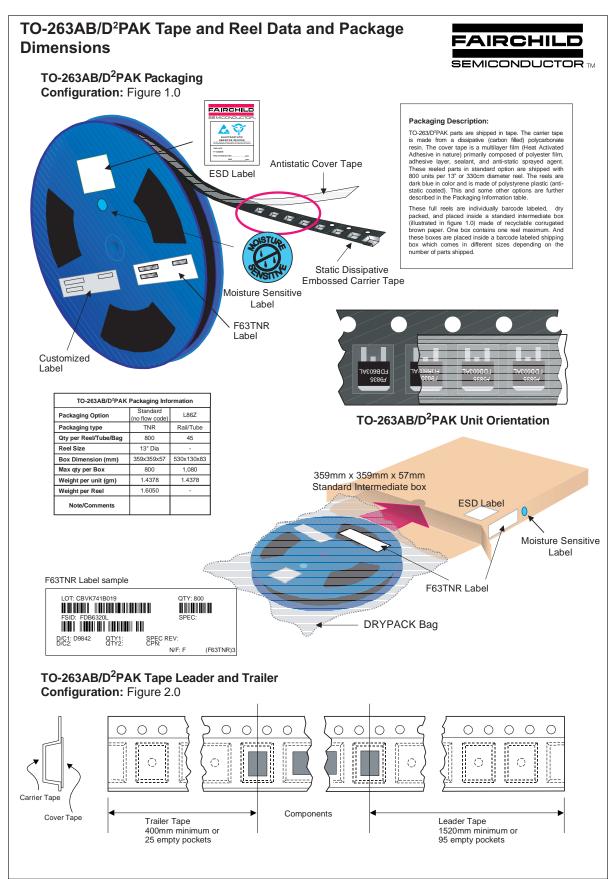


Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 1.4378

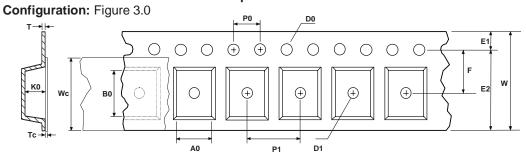


2. DIMENSION BASED ON JEDEC STANDARD TO-220 VARIATION AB, ISSUE J, DATED 3/24/87



TO-263AB/D²PAK Tape and Reel Data and Package Dimensions, continued

TO-263AB/D²PAK Embossed Carrier Tape



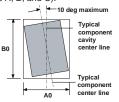
User Direction of Feed

Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
TO263AB/ D ² PAK (24mm)	10.60 +/-0.10	15.80 +/-0.10	24.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	22.25 min	11.50 +/-0.10	16.0 +/-0.1	4.0 +/-0.1	4.90 +/-0.10	0.450 +/-0.150	21.0 +/-0.3	0.06 +/-0.02

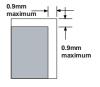
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

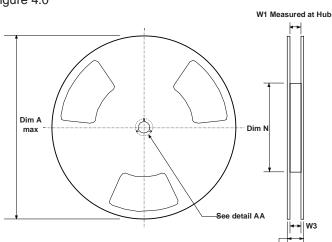


Sketch B (Top View)
Component Rotation

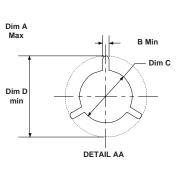


Sketch C (Top View)
Component lateral movement

TO-263AB/D²PAK Reel Configuration: Figure 4.0



13" Diameter Option



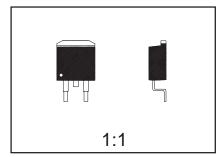
W2 max Measured at Hub

Dimensions are in inches and millimeters Reel Tape Size Dim A Dim B Dim C Dim D Dim N Dim W1 Dim W2 Dim W3 (LSL-USL) Option 512 +0.020/-0.008 13 +0.5/-0.2 0.961 +0.078/-0.000 24.4 +2/0 0.941 - 0.1.079 23.9 - 27.4 0.059 1.5 24mm 13" Dia

TO-263AB/D²PAK Tape and Reel Data and Package Dimensions, continued

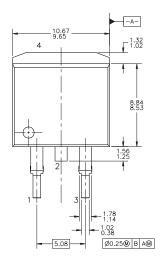
TO-263AB/D²PAK (FS PKG Code 45)

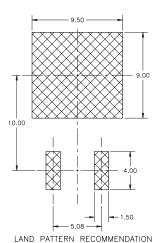


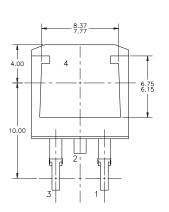


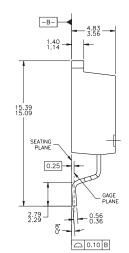
Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 1.4378









- NOTES: UNLESS OTHERWISE SPECIFIED

 A) ALL DIMENSIONS ARE IN MILLIMETERS.
 B) STANDARD LEAD FINISH:
 200 MICROINCHES / 5.08 MICROMETERS MIN.
 LEAD/TIN 15/85 ON OLIN 194 COPPER OR
 EQUIVALENT.
 C) MAXIMUM YERTICAL BURR ON HEATSINK NOT
 TO EXCEED 0.003 INCH / 0.05mm.
 D) NO PACKAGE CHIPS, CRACKS OR SURFACE
 IDENTIFICATION ALLOWED AFTER FORMING.
 E) REFERENCE JEDEC, TO—263, ISSUE C,
 VARIATION AB, DATED 2/92.

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